

AN 1989-246545 [34] WPIDS <<LOGINID::20090120>>  
DNC C1989-110238 [21]  
DNN N1989-187711 [21]  
TI Backing plate for sputtering target - containing  
copper comprising zinc, manganese, antimony, beryllium, calcium,  
chromium tellurium, yttrium and/or niobium, etc.  
DC M13; U11  
IN ISHIKURA C  
PA (TANI-C) TANAKA KIKINZOKU KOGYO KK  
CYC 1  
PIA JP 01180976 A 19890718 (198934)\* JA 3[3]  
ADT JP 01180976 A JP 1988-4094 19880112  
PRAI JP 1988-4094 19880112  
AB JP 01180976 A UPAB: 20050429  
Backing plate that constitutes sputtering targets,  
contains at least 99.7 weight% purity Cu, to which 100-3,000 weight  
ppm of at least one of Zn, Mn, Sb, Be, Ca, Cr, Te, Y, Nb, Mo,  
Ta, and Sn were added.  
USE - For mounting Cu clad sputtering  
target by metal bonding, preventing thermal pressure bonding with  
Cu substrate of clad target, capable of separating  
target material easily after sputtering.